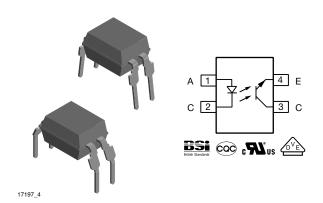
# TCET1201, TCET1202, TCET1203, TCET1204

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# **Optocoupler, Phototransistor Output**



#### LINKS TO ADDITIONAL RESOURCES



### **DESCRIPTION**

The TCET1200 consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 4 pin plastic dual inline package.

#### **FEATURES**

- High common mode rejection
- CTR offered in 5 groups
- · Low temperature coefficient of CTR
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





RoHS COMPLIANT

#### **APPLICATIONS**

- Switch-mode power supplies
- · Line receiver
- Computer peripheral interface
- Microprocessor system interface
- Reinforced isolation provides circuit protection against electrical shock (safety class II)
- Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):
  - for appl. class I IV at mains voltage  $\leq$  300 V
  - for appl. class I III at mains voltage ≤ 600 V according to DIN EN 60747-5-5 (VDE 0884-5)

### **AGENCY APPROVALS**

- <u>UL1577</u>
- cUL1577
- DIN EN 60747-5-5 (VDE 0884-5)
- BSI
- CQC GB8898-2011
- CQC GB4943.1-2011

ORDERING INFORMATION							
T C E	T 1	2 0	#	DIP			
_	PART NUMBER			7.62 mm			
AGENCY CERTIFIED / PACKAGE	CTR (%)						
AGENCY CENTIFIED / PACKAGE		10 mA					
UL, VDE, BSI, FIMKO	40 to 80	63 to 125	100 to 200	160 to 320			
DIP-4	TCET1201	TCET1202	TCET1203	TCET1204			

# TCET1201, TCET1202, TCET1203, TCET1204

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PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		$V_{R}$	6	V
Forward current		I <sub>F</sub>	60	mA
Forward surge current	t <sub>p</sub> ≤ 10 μs	I <sub>FSM</sub>	1.5	Α
Power dissipation		P <sub>diss</sub>	70	mW
Junction temperature		T <sub>j</sub>	125	°C
OUTPUT				
Collector emitter voltage		V <sub>CEO</sub>	70	V
Emitter collector voltage		V <sub>ECO</sub>	7	V
Collector current		Ic	50	mA
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I <sub>CM</sub>	100	mA
Power dissipation		P <sub>diss</sub>	70	mW
Junction temperature		Tj	125	°C
COUPLER				
Isolation test voltage (RMS)		V <sub>ISO</sub>	5000	V <sub>RMS</sub>
Total power dissipation		P <sub>tot</sub>	200	mW
Operating ambient temperature range		T <sub>amb</sub>	-40 to +100	°C
Storage temperature range		T <sub>stg</sub>	-55 to +125	°C
Soldering temperature (1)	2 mm from case, t ≤ 10 s	T <sub>sld</sub>	260	°C

#### Notes

<sup>(1)</sup> Refer to wave profile for soldering conditions for through hole devices

<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward voltage	$I_F = 50 \text{ mA}$	$V_{F}$	-	1.25	1.6	V		
Junction capacitance	$V_R = 0 V$ , $f = 1 MHz$	C <sub>j</sub>	-	50	-	pF		
OUTPUT								
Collector emitter voltage	I <sub>C</sub> = 1 mA	$V_{CEO}$	70	-	-	V		
Emitter collector voltage	I <sub>E</sub> = 100 μA	V <sub>ECO</sub>	7	-	-	V		
Collector emitter cut-off current	$V_{CE} = 20 \text{ V}, I_F = 0 \text{ A}, E = 0$	I <sub>CEO</sub>	-	10	100	nA		
COUPLER								
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V <sub>CEsat</sub>	-	-	0.3	V		
Cut-off frequency	$V_{CE}$ = 5 V, $I_F$ = 10 mA, $R_L$ = 100 $\Omega$	f <sub>c</sub>	-	110	-	kHz		
Coupling capacitance	f = 1 MHz	C <sub>k</sub>	-	0.6	-	pF		

#### Note

Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering
evaluations. Typical values are for information only and are not part of the testing requirements

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not
implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute
maximum ratings for extended periods of the time can adversely affect reliability

# TCET1201, TCET1202, TCET1203, TCET1204

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CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I <sub>C</sub> /I <sub>F</sub>	$V_{CE} = 5 \text{ V}, I_{F} = 5 \text{ mA}$	TCET1200	CTR	50	-	600	%
		TCET1201	CTR	40	-	80	%
	$V_{CF} = 5 \text{ V}, I_{F} = 10 \text{ mA}$	TCET1202	CTR	63	-	125	%
	V <sub>CE</sub> = 5 V, I <sub>F</sub> = 10 IIIA	TCET1203	CTR	100	-	200	%
		TCET1204	CTR	160	ı	320	%

SAFETY AND INSULATION RATED PARAMETERS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Partial discharge test voltage - routine test	100 %, t <sub>test</sub> = 1 s	V <sub>pd</sub>	1.6	-	-	kV	
Partial discharge test voltage - lot test (sample test)	t <sub>Tr</sub> = 60 s, t <sub>test</sub> = 10 s, (see Fig. 2)	V <sub>pd</sub>	1.36	-	-	kV	
Insulation resistance	V <sub>IO</sub> = 500 V	R <sub>IO</sub>	10 <sup>12</sup>	-	-	Ω	
	$V_{IO} = 500 \text{ V}, T_{amb} = 100 ^{\circ}\text{C}$	R <sub>IO</sub>	10 <sup>11</sup>	-	-	Ω	
	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 150 °C (construction test only)	R <sub>IO</sub>	10 <sup>9</sup>	-	-	Ω	
Rated impulse voltage		V <sub>IOTM</sub>	-	-	6	kV	
Max. working voltages	Recurring peak voltage	V <sub>IORM</sub>	850	-	-	V	
Forward current		I <sub>F</sub>	-	-	130	mA	
Power dissipation		P <sub>diss</sub>	-	-	265	mW	
Safety temperature		T <sub>si</sub>	-	-	150	°C	
Creepage distance			-	-	7.6	mm	

#### Note

 According to DIN EN 60747-5-2 (VDE 0884) (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits

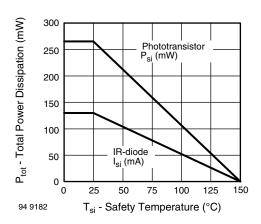


Fig. 1 - Derating Diagram

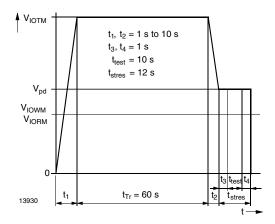


Fig. 2 - Test Pulse Diagram for Sample Test According to DIN EN 60747-5-5



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SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Delay time	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega, (\text{see Fig. 3})$	t <sub>d</sub>	-	3	-	μs	
Rise time	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega, (see Fig. 3)$	t <sub>r</sub>	=	3	-	μs	
Fall time	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega, \text{ (see Fig. 3)}$	t <sub>f</sub>	=	4.7	-	μs	
Storage time	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega, (\text{see Fig. 3})$	t <sub>s</sub>	-	0.3	-	μs	
Turn-on time	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega, (see Fig. 3)$	t <sub>on</sub>	=	6	-	μs	
Turn-off time	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega, \text{ (see Fig. 3)}$	t <sub>off</sub>	=	5	-	μs	
Turn-on time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega, \text{ (see Fig. 4)}$	t <sub>on</sub>	-	9	-	μs	
Turn-off time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega, \text{ (see Fig. 4)}$	t <sub>off</sub>	-	10	-	μs	

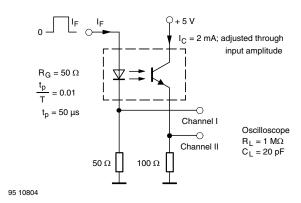


Fig. 3 - Test Circuit, Non-Saturated Operation

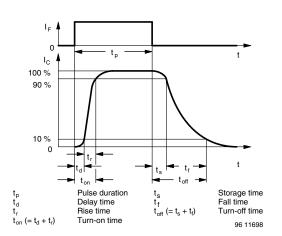


Fig. 5 - Switching Times

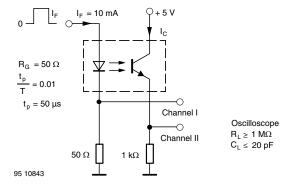


Fig. 4 - Test Circuit, Saturated Operation

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## **TYPICAL CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

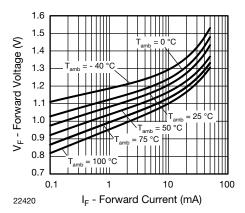


Fig. 6 - Forward Voltage vs. Forward Current

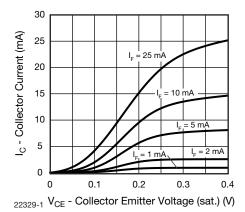


Fig. 9 - Collector Current vs. Collector Emitter Voltage (saturated)

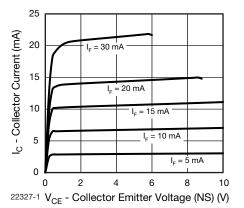


Fig. 7 - Collector Current vs. Collector Emitter Voltage (non-saturated)

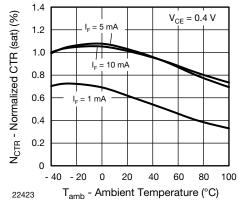


Fig. 10 - Normalized CTR (saturated) vs. Ambient Temperature

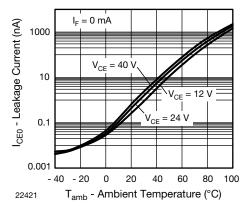


Fig. 8 - Leakage Current vs. Ambient Temperature

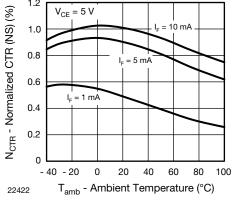


Fig. 11 - Normalized CTR (non-saturated) vs. Ambient Temperature

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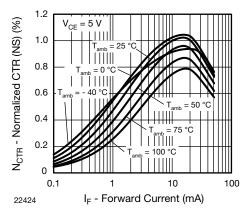


Fig. 12 - Normalized CTR (non-saturated) vs. Forward Current

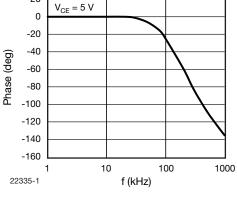


Fig. 15 - F<sub>CTR</sub> vs. Phase Angle (kHz)

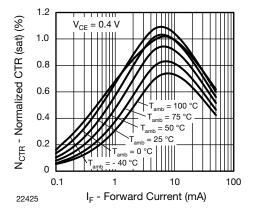


Fig. 13 - Normalized CTR (saturated) vs. Forward Current

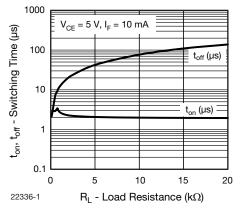


Fig. 16 - Switching Time vs. Load Resistance

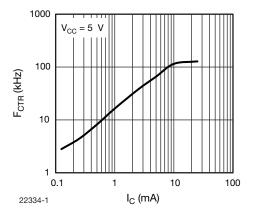
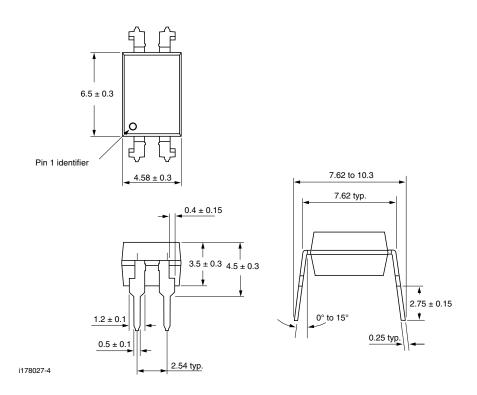


Fig. 14 -  $F_{CTR}$  vs.  $I_C$  (saturated) (mA)

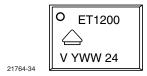
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### **PACKAGE DIMENSIONS** in millimeters



### **PACKAGE MARKING**



#### Note

• VDE logo is only printed on option 1 parts. Option information is not marked on the part



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